

Field
Sub
so that the entire surface of said semiconductor film is irradiated, while said lower surface of said substrate is in contact with said flat surface of the stage.

10. (Thrice Amended) A method of manufacturing a liquid crystal display device comprising the steps of:

Sub
forming a semiconductor film over a substrate having an upper surface and a lower surface, wherein said upper surface is an insulating surface;

Fig
flattening said substrate by vacuum-sucking said substrate onto a stage having a flat surface and at least one suction inlet in such a manner that said lower surface of said substrate is in contact with said flat surface of the stage; and

irradiating said semiconductor film with a laser beam having a cross section which is elongated in one direction while relatively moving said substrate with respect to said laser beam so that the entire surface of said semiconductor film is irradiated, while said lower surface of said substrate is in contact with said flat surface of the stage.

13. (Thrice Amended) A method of manufacturing a liquid crystal display device comprising the steps of:

Sub
Fig 3
forming a semiconductor film over a substrate having an upper surface and a lower surface, wherein said upper surface is an insulating surface;

heating said substrate;

flattening said substrate by vacuum-sucking said substrate onto a stage having a flat surface in such a manner that said lower surface of said substrate is in contact with said flat surface of the stage; and

Sub 13
F3/enc
irradiating said semiconductor film with a laser beam having a cross section which is elongated in one direction while relatively moving said substrate with respect to said laser beam so that the entire surface of said semiconductor film is irradiated, while said lower surface of said substrate is in contact with said flat surface of the stage.

16. (Thrice Amended) A method of manufacturing a liquid crystal display device comprising the steps of:

Sub 13
F4
forming a semiconductor film over a substrate having an upper surface and a lower surface, wherein said upper surface is an insulating surface;

heating said substrate;

flattening said substrate by vacuum-sucking said substrate onto a stage having a flat surface and at least one suction inlet in such a manner that said lower surface of said substrate is in contact with said flat surface of the stage; and

irradiating said semiconductor film with a laser beam having a cross section which is elongated in one direction while relatively moving said substrate with respect to said laser beam so that the entire surface of said semiconductor film is irradiated, while said lower surface of said substrate is in contact with said flat surface of the stage.

19. (Thrice Amended) A method of manufacturing a liquid crystal display device comprising the steps of:

F5
Sub 13
forming a semiconductor film over a substrate having an upper surface and a lower surface, wherein said upper surface is an insulating surface;

heating substrate to crystallize said semiconductor film;

flattening said substrate by vacuum-sucking said substrate onto a stage having a flat surface in such a manner that said lower surface of said substrate is in contact with said flat surface of the stage; and

irradiating the crystallized semiconductor film over said substrate provided on said stage with a laser beam having a cross section which is elongated in one direction while relatively moving said substrate with respect to said laser beam so that the entire surface of said semiconductor film is irradiated.

22. (Thrice Amended) A method of manufacturing a liquid crystal display device comprising the steps of:

forming a semiconductor film over a substrate having an upper surface and a lower surface, wherein said upper surface is an insulating surface;

heating substrate to crystallize said semiconductor film;

flattening said substrate by vacuum-sucking said substrate onto a stage having a flat surface and at least one suction inlet in such a manner that said lower surface of said substrate is in contact with said flat surface of the stage; and

irradiating the crystallized semiconductor film with a laser beam having a cross section which is elongated in one direction while relatively moving said substrate with respect to said laser beam so that the entire surface of said semiconductor film is irradiated, while said lower surface of said substrate is in contact with said flat surface of the stage.

Cancel claims 31-36 and 45-46.